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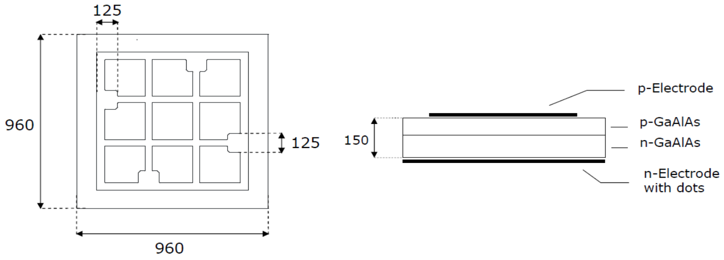
EPIGAP

Data Sheet

LED Chip Infrared EOLC-770-11

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs, DDH	P (anode) up



Typ. thickness: 150±30 µm
Anode: gold alloy, thickness 1.5 µm
Cathode: gold alloy, thickness 0.5 µm, structured, 25% covered

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		1.5	2	V
Forward voltage	I_F=350 mA	V_F		1.8		V
Reverse voltage	I_R=100 µA	V_R	5			V
Radiant power*	I_F=20 mA	Φ_e	2.5	3.5		mW
Radiant power*	I_F=350 mA	Φ_e		70		mW
Peak wavelength	I_F=350 mA	λ_p	760	770	780	nm
FWHM	I_F=350 mA	$\Delta\lambda_{0.5}$		30		nm
Switching time	I_F=20 mA	t_r, t_f		15		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No. 113 016

RoHS COMPLIANT

Pb Pb-Free